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Nota di contenuto	<p>Nitride Semiconductors Handbook on Materials and Devices; Contents; Preface; List of Contributors; Part 1 Material; 1 High-Pressure Crystallization of GaN; 1.1 Introduction; 1.2 High-Pressure Crystallization of GaN; 1.2.1 Thermodynamics - Properties of GaN-Ga-N(2) System; 1.2.2 Dissolution Kinetics of N(2) and Crystal Growth Mechanism; 1.2.3 What Happens with GaN at High Temperature when the N(2) Pressure is too Low?; 1.2.4 Crystallization of GaN Using High Nitrogen Pressure Solution Growth (HNPSG) Method - Experimental; 1.2.5 Properties of GaN Single Crystals Obtained by HNPSG Method 1.2.5.1 Crystals Grown without Intentional Seeding 1.2.5.2 Seeded Growth of GaN by HNPS Method; 1.2.6 Physical Properties of GaN Crystals, Grown by HNPS Method; 1.2.6.1 Point Defects; 1.2.6.2 Extended Defects; 1.3 Epitaxy on Bulk GaN; 1.3.1 Introduction; 1.3.2 Metalorganic Chemical Vapor Epitaxy on GaN Substrates in HPRC Unipress; 1.3.3 Molecular Beam Epitaxy; 1.4 Optoelectronic Devices; 1.4.1 Introduction; 1.4.2 Light Emitting Diodes Fabricated on Bulk GaN in HPRC; 1.4.3 Laser Diode Structures; 1.5 Conclusions; 1.6 Acknowledgment; 1.7 References; 2 Epitaxial Lateral Overgrowth of GaN</p> <p>2.1 Heteroepitaxial GaN 2.1.1 Introduction; 2.1.2 Growth of GaN/Sapphire and 6H-SiC Templates; 2.1.2.1 2D Growth Mode (GaN/Sapphire); 2.1.2.2 3D Growth Mode (GaN/Sapphire); 2.1.3 Defects in GaN/Sapphire and GaN/6H-SiC; 2.1.3.1 Extended Defects; 2.1.3.2 Native Defects; 2.1.3.3 Defect-Related Optical Properties; 2.1.3.4 Device Performance Limitations; 2.1.3.5 Electronic Properties of Defects; 2.2 Epitaxial Lateral Overgrowth (ELO); 2.2.1 Standard ELO; 2.2.2 Rationale; 2.2.3 Experimental; 2.3 One-Step Lateral Overgrowth (1S-ELO); 2.3.1 ELO in MOVPE; 2.3.1.1 Morphology and Defects 2.3.1.2 Structural Assessment 2.3.1.3 Kinetics; 2.3.1.4 In-Depth Optical Assessment of MOVPE ELO GaN; 2.3.2 HVPE; 2.3.2.1 In-Depth Assessment of HVPE ELO GaN; 2.3.2.2 Stripe Openings along ; 2.3.2.3 Selective Area Epitaxy (SAE); 2.3.2.4 (C(2)H(5))(2)GaCl as Ga Source; 2.3.2.5 Stress Generation; 2.3.3 Sublimation; 2.3.4 New Developments; 2.3.4.1 ELO on Si; 2.3.4.2 Using W as Mask; 2.3.4.3 Maskless ELO; 2.3.5 Improvements of the Standard ELO Method; 2.3.6 Pendoe-Epitaxy; 2.3.7 ELO of Cubic GaN; 2.4 Two-Step ELO (2S-ELO); 2.4.1 Experimental (MOVPE); 2.4.2 In-Depth Assessment of 2S-ELO 2.4.2.1 Cathodoluminescence 2.4.2.2 Luminescence of GaN by Epitaxial Lateral Overgrowth; 2.4.2.3 Time-resolved Photoluminescence; 2.4.2.4 Deep Level Transient Spectroscopy (DLTS); 2.4.2.5 Strain Distribution; 2.4.3 Assessment of HVPE; 2.4.4 ELO and Yellow Luminescence; 2.4.5 Conclusion; 2.5 New Trends; 2.5.1 3S-ELO; 2.5.2 Further Improvements; 2.6 Theoretical Analysis of ELO; 2.7 Acknowledgments; 2.8 References; 3 Plasma-Assisted Molecular Beam Epitaxy of III-V Nitrides; 3.1 Introduction; 3.2 The Nitrogen Plasma Source; 3.2.1 The Different Sources; 3.2.2 The Nitrogen Plasma 3.2.3 Characterization of the HD25 RF Source by Optical Emission Spectroscopy</p>
Sommario/riassunto	<p>Semiconductor components based on silicon have been used in a wide range of applications for some time now. These elemental semiconductors are now well researched and technologically well developed. In the meantime the focus has switched to a new group of materials: ceramic semiconductors based on nitrides are currently the subject of research due to their optical and electronic characteristics. They open up new industrial possibilities in the field of photosensors,</p>

as light sources or as electronic components. This collection of review
articles provides a systematic and in-depth overview o
